



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2813  
#5/A  
8/30/02  
Mollie

In re the Application of:

**YASUMOTO, Tamihide**

Group Art Unit: **2813**

Serial No.: **09/995,575**

Examiner: **KIELIN, E.**

Filed: **November 29, 2001**

P.T.O. Confirmation No.: **1497**

For: **SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING**

**AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

August 20, 2002

Sir:

In response to the Office Action dated June 5, 2002, please amend the above-identified application as follows:

**IN THE ABSTRACT:**

A1  
LAST  
page

Please delete the current Abstract and replace therewith the attached substitute Abstract.

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**IN THE SPECIFICATION:**

**Please replace the paragraph at page 2, lines 13-23 with the following rewritten paragraph:**

A2

According to one aspect of the present invention, there is provided a method for manufacturing a semiconductor device, comprising the steps of: forming a wiring comprising silicon on a surface of a semiconductor substrate; covering part of the wiring with a resist pattern; implanting ions into the wiring